

NTE5646 TRIAC – Internally Triggered

Description:

The NTE5646 is a TRIAC that includes a diac trigger mounted inside the same package. This device saves the user the added expense of buying a discrete diac and the assembling associated with a gated triac. This device includes a dial trigger mounted inside the same isolated TO220 type package.

Absolute Maximum Ratings:

Repetitive Peak Off–State Voltage (Gate Open, T _J = +110°C, Note 1), V _{DRM}	V00
RMS On–State Current (T _C = +80°C, Conduction Angle of 360°), I _{T(RMS)}	10A
Peak Surge (Non-Repetitive) On-State Current (One Cycle, at 50Hz or 60Hz), I _{TSM}	A00
Peak Gate-Trigger Current (3sec Max), I _{GTM} 1	.5A
Operating Junction Temperature Range, Topr—40° to +110	0°C
Storage Temperature Range, T _{stg} –40° to +15	0°C
Typical Thermal Resistance, Junction to Case, R _{⊖JC}	C/W

Note 1. All values apply in either direction.

Electrical Characteristics: $(T_C = +25^{\circ}C \text{ unless otherwise specified})$

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit		
Peak Off-State Current	I _{DRM}	Gate Open, $T_V = +110$ °C, $V_{DRM} = 600$ V, Note 1	_	0.5	_	mA		
Maximum On-State Voltage	V_{TM}	I _T = 10A, Note 1	_	_	1.5	V		
DC Holding Current	I _{HOLD}	Gate Open, Note 1	_	_	60	mA		
Critical Rate-of-Rise of Off-State Voltage	Critical dv/dt	$V_D = 600V$, Gate Open, $T_C = +110C$, Note 1	_	60	_	V/μs		
Critical Rate-of-Rise of Commutation Voltage	Commutating dv/dt	$T_C = +80$ °C, Gate Unenergized, $V_D = 600$ V, $I_T = 10$ A, Note 1	_	4	_	V/μs		
Gate-Controlled Turn-On Time	T_{gt}	$V_D = 600V, t_R = 0.1 \mu s,$ $I_T = 10A (Peak)$	_	3	_	μs		
Trigger DIAC Specifications								
Breakover Voltage Symmetry	$\Delta V_{(BO)}$		_	3	_	V		
Breakover Voltage (Forward & Reverse)	V_{BO}		30	_	45	V		
Dynamic Breakback Voltage (Forward & Reverse)	[ΔV ±]		1	5	_	V		
Peak Breakover Current	I _{BO}		1	200	_	μΑ		
Trigger Firing Capacitance	С		-	0.1	_	μF		

Note 1. All values apply in either direction.

